

2SC5632

Silicon NPN epitaxial planer type

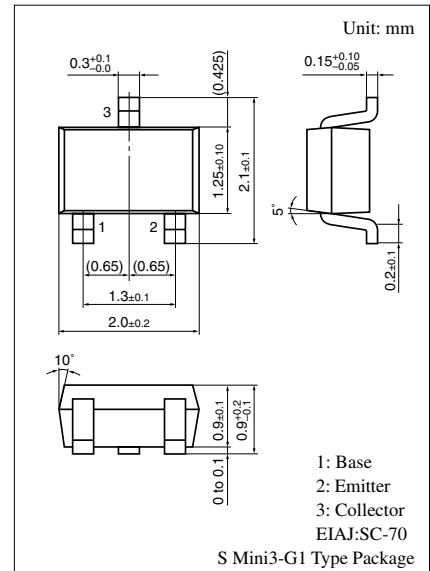
For high-frequency amplification and switching

■ Features

- High transition frequency f_T
- Smini3-G1 type package, allowing downsizing and thinning of the equipment and automatic insertion through the tape packing

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	15	V
Collector to emitter voltage	V_{CEO}	8	V
Emitter to base voltage	V_{EBO}	3	V
Collector current	I_C	50	mA
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$



Marking Symbol: 2R

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Emitter cutoff current	I_{EBO}	$V_{EB} = 2\text{ V}, I_C = 0$			2	μA
Collector to base voltage	V_{CBO}	$I_C = 100\ \mu\text{A}, I_E = 0$	15			V
Forward current transfer ratio	h_{FE}	$V_{CE} = 4\text{ V}, I_C = 2\text{ mA}$	100		350	
Ratio forward current transfer ratio	$h_{FE(\text{RATIO})}$	$V_{CE} = 4\text{ V}, I_C = 100\ \mu\text{A}/2\text{ mA}$	0.6		1.5	
Collector to emitter saturation voltage	$V_{CE(\text{sat})}$	$I_C = 20\text{ mA}, I_B = 4\text{ mA}$			0.5	V
Collector output capacitance	C_{ob}	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$		1.0	1.6	pF
Transition frequency	f_T	$V_{CE} = 5\text{ V}, I_C = 15\text{ mA}, f = 200\text{ MHz}$	0.6	1.1		GHz